

ABSTRACT OF THE DISCLOSURE

A method for etching a tungsten-containing layer (525) on a substrate (510) substantially anisotropically, with good etching selectivity with respect to a hard mask layer, and without forming excessive passivating deposits on the etched features. In the method, the substrate (510) is placed in a plasma zone, and process gas mix comprising NF₃ and Cl₂ is introduced into the plasma zone. A plasma is formed from the process gas mix to anisotropically etch the tungsten containing layer (525) to produce patterned tungsten features (535).